Onsemi

General Purpose Transistors

NPN Silicon

2N3903, 2N3904

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

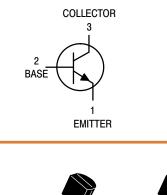
Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	40	Vdc
Collector - Base Voltage	V _{CBO}	60	Vdc
Emitter – Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	۱ _C	200	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

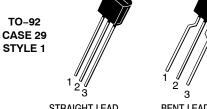
THERMAL CHARACTERISTICS (Note 1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	R _{0JC}	83.3	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Indicates Data in addition to JEDEC Requirements.



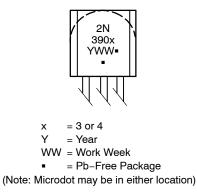


STRAIGHT LEAD **BULK PACK**

TO-92

BENT LEAD TAPE & REEL AMMO PACK

MARKING DIAGRAMS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25° C unless otherwise noted)

Characterist	ic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector - Emitter Breakdown Voltage (Note 2) (I	_C = 1.0 mAdc, I _B = 0)	V _{(BR)CEO}	40	-	Vdc
Collector – Base Breakdown Voltage ($I_C = 10 \ \mu Ac$	lc, I _E = 0)	V _{(BR)CBO}	60	-	Vdc
Emitter – Base Breakdown Voltage (I _E = 10 μ Adc	, I _C = 0)	V _{(BR)EBO}	6.0	-	Vdc
Base Cutoff Current (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc	dc)	I _{BL}	-	50	nAdc
Collector Cutoff Current (V _{CE} = 30 Vdc, V _{EB} = 3.	0 Vdc)	I _{CEX}	-	50	nAdc
ON CHARACTERISTICS				•	
DC Current Gain (Note 2) $(I_C = 0.1 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$	2N3903 2N3904	h _{FE}	20	_	-
(I _C = 1.0 mAdc, V _{CE} = 1.0 Vdc)	2N3903		40 35	-	
$(I_{C} = 10 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$	2N3904 2N3903 2N3904		70 50 100	- 150 300	
$(I_C = 50 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$	2N3903 2N3904		30	-	
(I _C = 100 mAdc, V _{CE} = 1.0 Vdc)	2N3904 2N3903 2N3904		60 15 30	-	
		V _{CE(sat)}		0.2 0.3	Vdc
$\begin{array}{l} \text{Base}-\text{Emitter Saturation Voltage (Note 2)} \\ (I_{C}=10 \text{ mAdc}, I_{B}=1.0 \text{ mAdc}) \\ (I_{C}=50 \text{ mAdc}, I_{B}=5.0 \text{ mAdc}) \end{array}$		V _{BE(sat)}	0.65	0.85 0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS				•	
Current – Gain – Bandwidth Product ($I_C = 10 \text{ mAdc}, V_{CE} = 20 \text{ Vdc}, f = 100 \text{ MHz}$)	2N3903 2N3904	f _T	250 300		MHz
Output Capacitance (V _{CB} = 5.0 Vdc, I _E = 0, f = 1	.0 MHz)	C _{obo}	-	4.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I_C = 0, f = 1.0	MHz)	C _{ibo}	-	8.0	pF
Input Impedance (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h _{ie}	1.0 1.0	8.0 10	kΩ
Voltage Feedback Ratio ($I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz}$)	2N3903 2N3904	h _{re}	0.1 0.5	5.0 8.0	X 10-
Small–Signal Current Gain (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h _{fe}	50 100	200 400	-
Output Admittance (I _C = 1.0 mAdc, V_{CE} = 10 Vdc	c, f = 1.0 kHz)	h _{oe}	1.0	40	μmho
Noise Figure (I_C = 100 μ Adc, V _{CE} = 5.0 Vdc, R _S = 1.0 k Ω , f =	1.0 kHz) 2N3903 2N3904	NF		6.0 5.0	dB
SWITCHING CHARACTERISTICS				1	
Delay Time (V _{CC} = 3.0 Vdc, V _{BE} = 0.5	5 Vdc.	t _d	-	35	ns
Rise Time $I_C = 10 \text{ mAdc}, I_{B1} = 1.0 \text{ m}$		t _r	_	35	ns

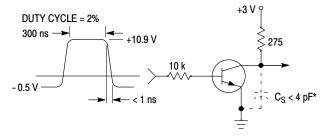
Delay Time	(V _{CC} = 3.0 Vdc, V _{BE} = 0.5 Vdc,	t _d	-	35	ns
Rise Time	$I_{C} = 10 \text{ mAdc}, I_{B1} = 1.0 \text{ mAdc})$	t _r	-	35	ns
Storage Time		t _s	-	175 200	ns
Fall Time		t _f	-	50	ns

2. Pulse Test: Pulse Width \leq 300 µs; Duty Cycle \leq 2%.

ORDERING INFORMATION

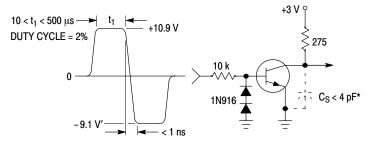
Device	Package	Shipping [†]
2N3903RLRM	TO-92	2000 / Ammo Pack
2N3904	TO-92	5000 Units / Bulk
2N3904G	TO-92 (Pb-Free)	5000 Units / Bulk
2N3904RLRA	TO-92	2000 / Tape & Reel
2N3904RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904RLRM	TO-92	2000 / Ammo Pack
2N3904RLRMG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RLRP	TO-92	2000 / Ammo Pack
2N3904RLRPG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904ZL1	TO-92	2000 / Ammo Pack
2N3904ZL1G	TO-92 (Pb-Free)	2000 / Ammo Pack

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



* Total shunt capacitance of test jig and connectors

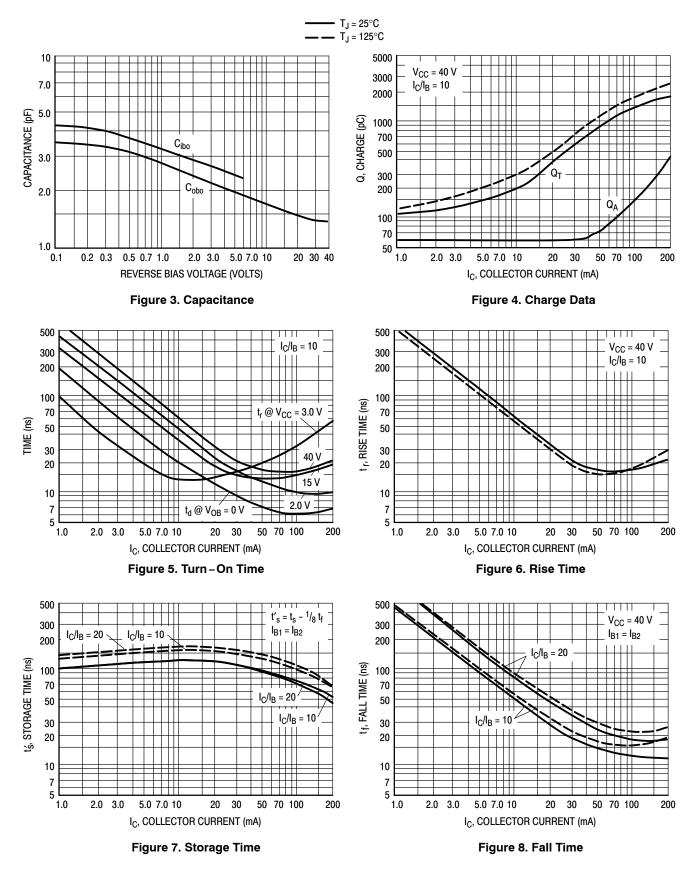
Figure 1. Delay and Rise Time Equivalent Test Circuit



* Total shunt capacitance of test jig and connectors

Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS



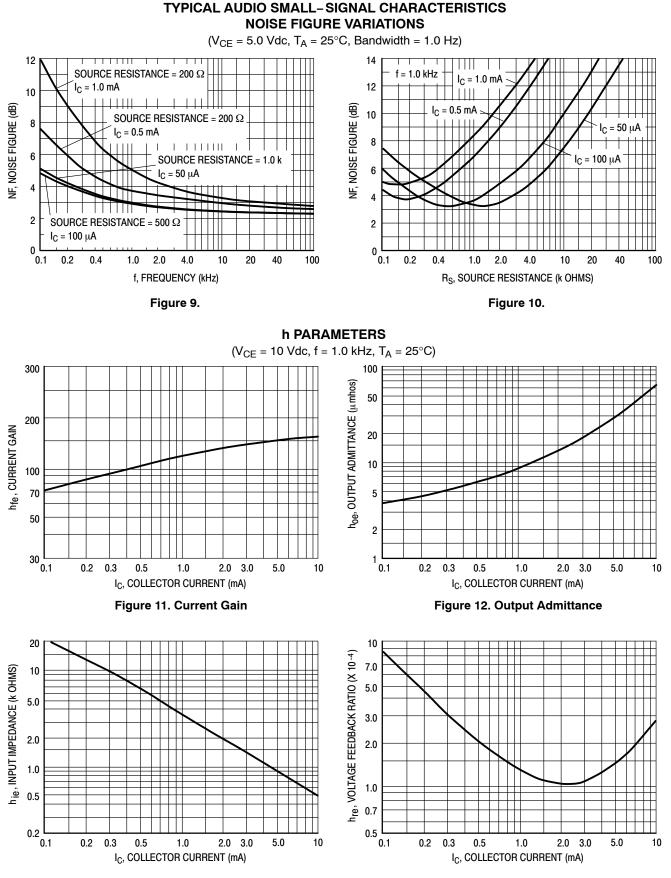
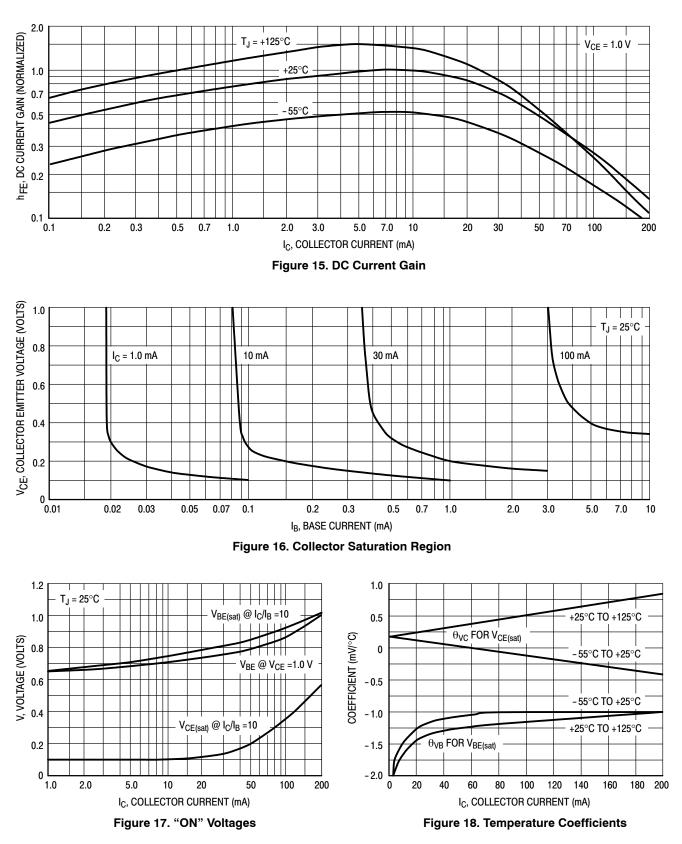


Figure 13. Input Impedance

Figure 14. Voltage Feedback Ratio

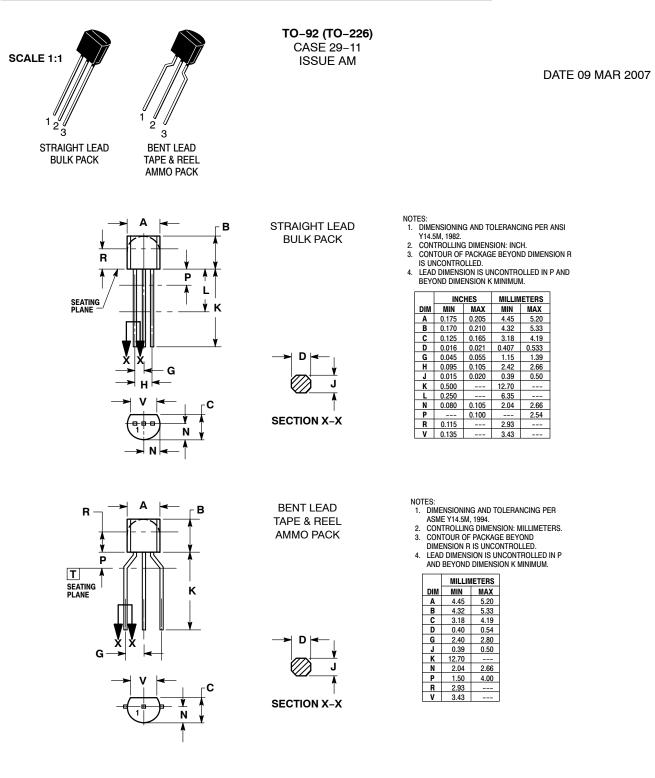
TYPICAL STATIC CHARACTERISTICS



MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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STYLES ON PAGE 2

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DATE 09 MAR 2007

STYLE 1: PIN 1. EMITTER 2. BASE 3. COLLECTOR STYLE 6: PIN 1. GATE 2. SOURCE & SUBSTRATE 3. DRAIN STYLE 11: PIN 1. ANODE 2. CATHODE & ANODE 3. CATHODE STYLE 16: PIN 1. ANODE 2. GATE 3. CATHODE STYLE 21: PIN 1. COLLECTOR 2. EMITTER 3. BASE STYLE 22: PIN 1. VCC 2. GROUND 2 3. OUTPUT STYLE 31: PIN 1. GATE 2. DRAIN 3. SOURCE

	BASE EMITTER COLLECTOR
2.	SOURCE DRAIN GATE
2.	MAIN TERMINAL 1 Gate Main Terminal 2
2.	COLLECTOR BASE EMITTER
2.	SOURCE GATE DRAIN

2	1. 2.	ANODE ANODE CATHODE
2	1. 2.	DRAIN Gate Source & Substrate
2	1. 2.	ANODE 1 GATE CATHODE 2
2	1. 2.	ANODE CATHODE NOT CONNECTED
2	1. 2.	GATE SOURCE DRAIN
2	1. 2.	CATHODE ANODE GATE

STYLE 33: PIN 1. RETURN 2. INPUT 3. OUTPUT

2.	CATHODE CATHODE ANODE
2.	BASE 1 EMITTER BASE 2
2.	EMITTER COLLECTOR BASE
	GATE ANODE CATHODE
2.	EMITTER Collector/Anode Cathode
2.	NOT CONNECTED ANODE CATHODE
2.	INPUT GROUND LOGIC

STYLE 4:

STYLE 5: PIN 1. DRAIN 2. SOURCE 3. GATE STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE STYLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 STYLE 20: PIN 1. NOT CONNECTED 2. CATHODE 3. ANODE STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2 STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE STYLE 35: PIN 1. DRAIN 2. GATE 3. SOURCE STYLE 35: PIN 1. GATE 2. COLLECTOR 3. EMITTER

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